





Interaction of oxygen with plasma-deposited Si:N:H primer coatings

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Introduction

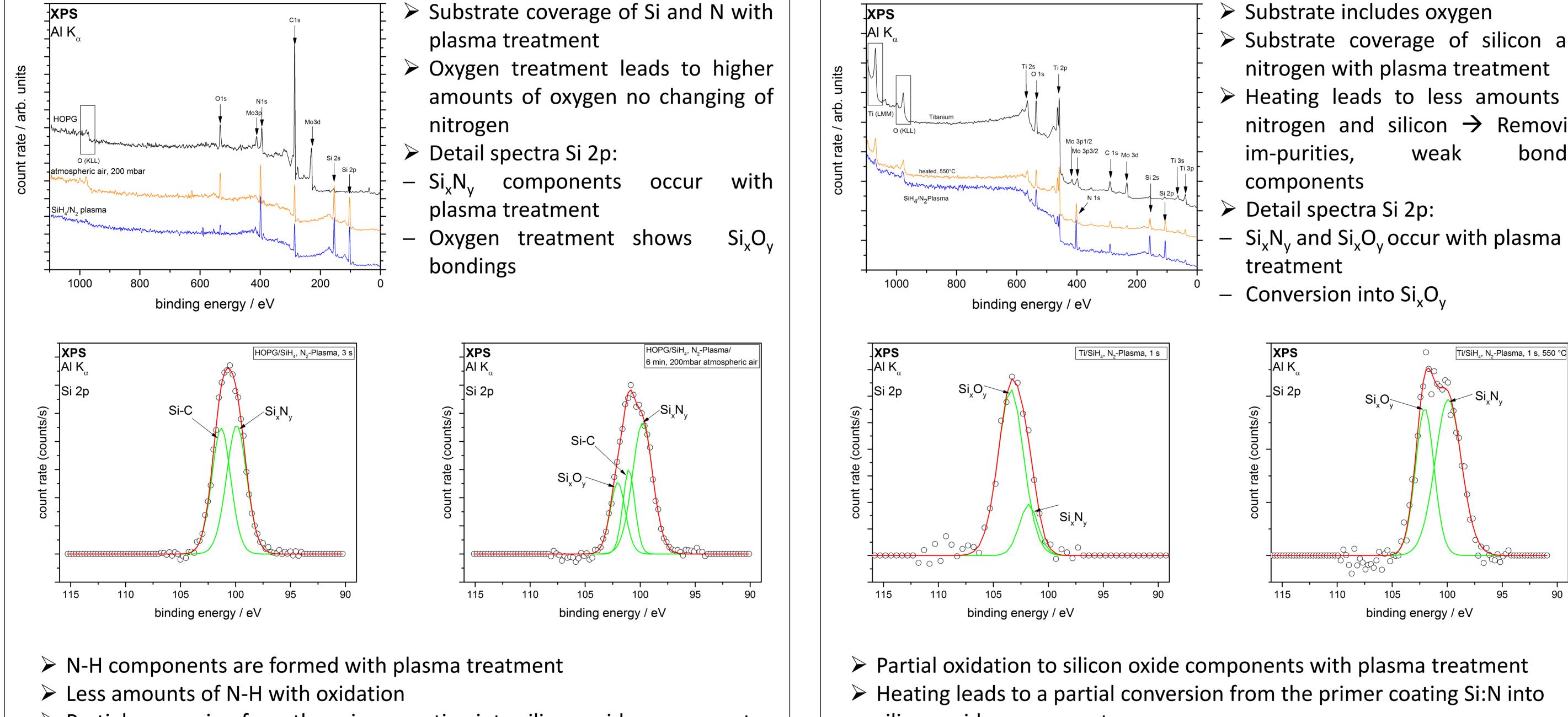
Silicon dioxide coatings are applied via a two step process using a dielectric barrier discharge (DBD) plasma treatment. In the first processing step a mixture of silane and nitrogen is employed for the DBD plasma treatment to deposit the primer Si:N:H coating. In the second step the primer coating is exposed to oxygen plasma treatment for a conversion into stoichiometric silicon dioxide. Without any plasma treatment small amounts of oxygen show a partial conversion of the primer coating. This high reactivity against oxygen is now investigated by small vapor pressures of atmospheric air in a ultra-high vacuum chamber on highly oriented pyrolytic graphite (HOPG) as substrate. This is compared to the interaction of the primer coating with an oxidic substrate while heating. Titanium due to its oxidated surface is used for substrate. To study the differences between the two ways of partial conversion of the primer coating X-ray photoelectron spectroscopy (XPS), photoemission spectroscopy (UPS) and metastable impact electron spectroscopy (MIES) are employed.

Interaction of primer coating with atmospheric air

Interaction of primer coating with oxidic substrate

Experimental:

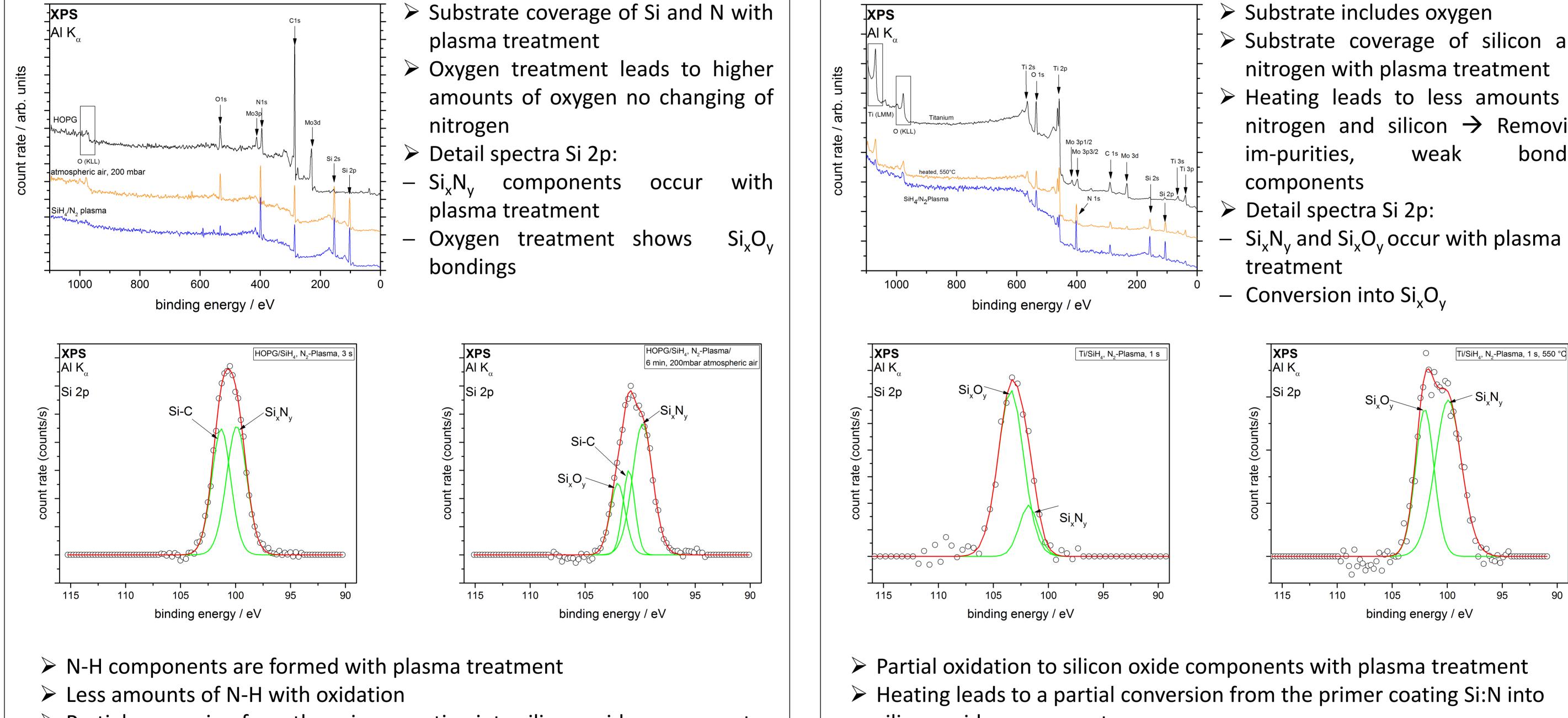
- HOPG substrate (black spectrum)
- \succ Plasma Treatment: DBD, 1 mm distance, 3 s, 200 mbar SiH₄/N₂ (blue spectrum)
- > Oxygen exposure in 200 mbar atmospheric air, 6 min (orange spectrum)



Experimental:

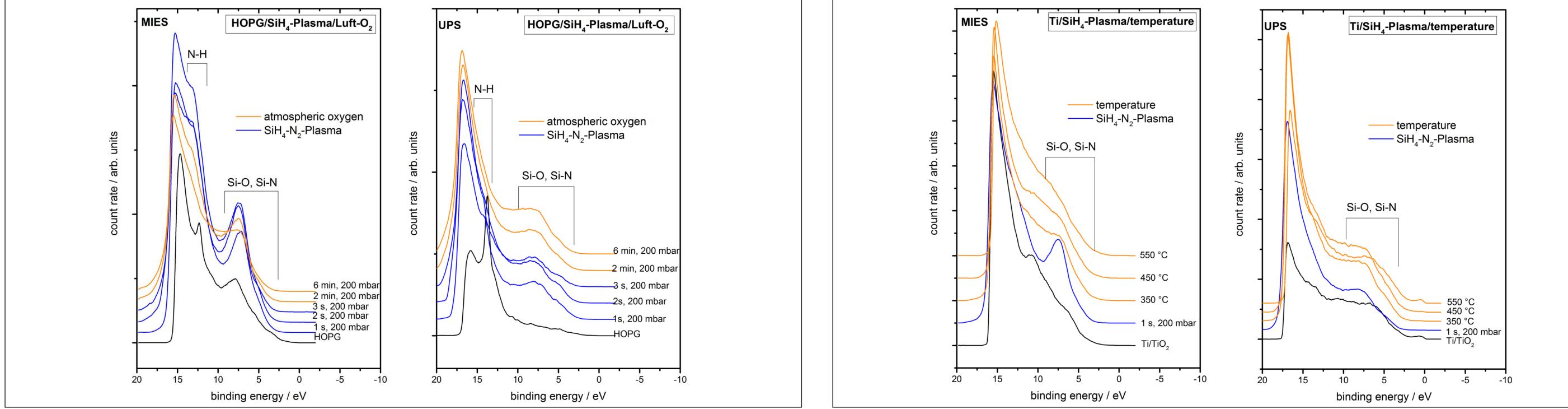
 \succ Ti with TiO₂ substrate (black spectrum)

 \succ Plasma treatment: DBD, 1 mm distance, 1 s, 200 mbar SiH₄/N₂ (blue spectrum) > Oxygen exposure: heating substrate 550 °C



- Substrate coverage of silicon and
- > Heating leads to less amounts of nitrogen and silicon \rightarrow Removing bonded

> Partial conversion from the primer coating into silicon oxide components



silicon oxide components Desorption of Si-O and Si-N components while heating

